

STEALTH™ Diode

18 A, 1200 V

ISL9R18120G2, ISL9R18120S3S

Description

The ISL9R18120G2, ISL9R18120S3S is a STEALTH diode optimized for low loss performance in high frequency hard switched applications. The STEALTH family exhibits low reverse recovery current (I_{RR}) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low I_{RR} and short t_a phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Features

- Stealth Recovery $t_{rr} = 300$ ns (@ $I_F = 18$ A)
- Max Forward Voltage, $V_F = 3.3$ V (@ $T_C = 25^\circ\text{C}$)
- 1200 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- These Devices are Pb-Free and are RoHS Compliant

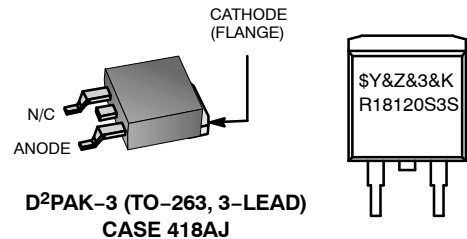
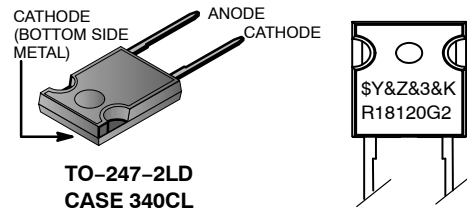
Applications

- Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- Snubber Diode



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MARKING DIAGRAM

\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
R18120G2, R18120S3S	= Specific Device Code

SYMBOL



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ISL9R18120G2, ISL9R18120S3S

DEVICE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	1200	V
Working Peak Reverse Voltage	V _{RWM}	1200	V
DC Blocking Voltage	V _R	1200	V
Average Rectified Forward Current (T _C = 92°C)	I _{F(AV)}	18	A
Repetitive Peak Surge Current (20 kHz Square Wave)	I _{FRM}	36	A
Non-repetitive Peak Surge Current (Halfwave 1 Phase 60 Hz)	I _{FSM}	200	A
Power Dissipation	P _D	125	W
Avalanche Energy (1 A, 40 mH)	E _{AVL}	20	mJ
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C
Maximum Temperature for Soldering Leads at 0.063 in (1.6 mm) from Case for 10 s Package Body for 10 s	T _L T _{PKG}	300 260	°C °C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Packing Method	Tape Width	Quantity
ISL9R18120G2	R18120G2	TO-247-2LD	Tube	N/A	30
ISL9R18120S3ST	R18120S3S	TO-263-3LD (D ² -PAK)	Reel	24 mm	800

THERMAL CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Thermal Resistance Junction to Case	R _{θJC}	TO-247, TO-263	-	-	1.0	°C/W
Thermal Resistance Junction to Ambient	R _{θJA}	TO-247	-	-	30	°C/W
Thermal Resistance Junction to Ambient	R _{θJA}	TO-263	-	-	62	°C/W

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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Off State Characteristics

Instantaneous Reverse Current	I _R	V _R = 1200 V	T _C = 25°C	-	-	100	μA
			T _C = 125°C	-	-	1.0	mA

On State Characteristics

Instantaneous Forward Voltage	V _F	I _F = 18 A	T _C = 25°C	-	2.7	3.3	V
			T _C = 125°C	-	2.5	3.1	V

Dynamic Characteristics

Junction Capacitance	C _J	V _R = 10 V, I _F = 0 A	-	69	-	pF
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Switching Characteristics

Reverse Recovery Time	t _{rr}	I _F = 1 A, dI _F /dt = 100 A/μs, V _R = 30 V	-	38	45	ns	
		I _F = 18 A, dI _F /dt = 100 A/μs, V _R = 30 V	-	60	70	ns	
Reverse Recovery Time	t _{rr}	I _F = 18 A, dI _F /dt = 200 A/μs, V _R = 780 V, T _C = 25°C	-	300	-	ns	
Reverse Recovery Current	I _{rr}		-	6.5	-	A	
Reverse Recovered Charge	Q _{rr}		-	950	-	nC	
Reverse Recovery Time	t _{rr}		-	400	-	ns	
Softness Factor (t _b /t _a)	S		-	7.0	-	-	
Reverse Recovery Current	I _{rr}	I _F = 18 A, dI _F /dt = 200 A/μs, V _R = 780 V, T _C = 125°C	-	8.0	-	A	
Reverse Recovered Charge	Q _{rr}		-	2.0	-	μC	
Reverse Recovery Time	t _{rr}		I _F = 18 A, dI _F /dt = 1000 A/μs, V _R = 780 V, T _C = 125°C	-	235	-	ns
Softness Factor (t _b /t _a)	S			-	5.2	-	-
Reverse Recovery Current	I _{rr}			-	22	-	A
Reverse Recovered Charge	Q _{rr}	-		2.1	-	μC	
Maximum di/dt During t _b	dI _M /dt	-		370	-	A/μs	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL PERFORMANCE CURVES

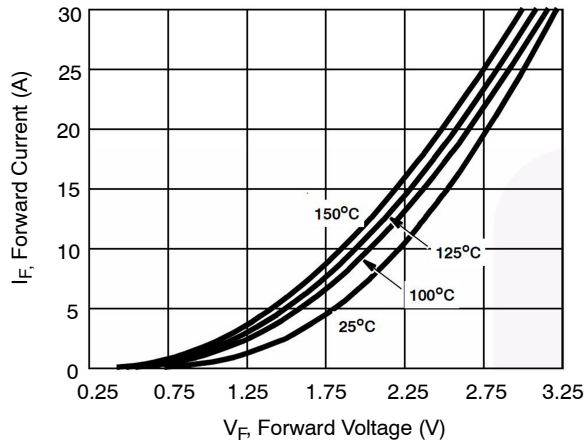


Figure 1. Forward Current vs. Forward Voltage

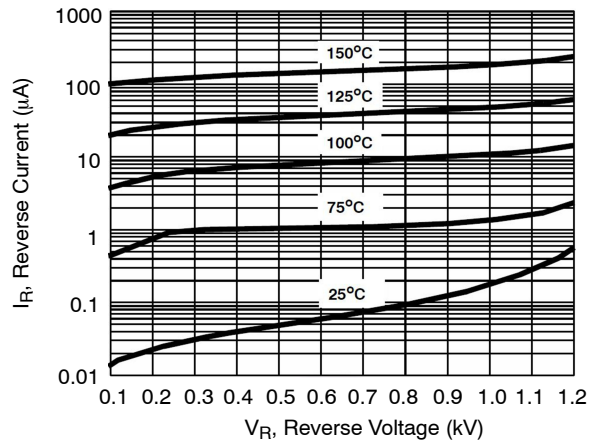


Figure 2. Reverse Current vs. Reverse Voltage

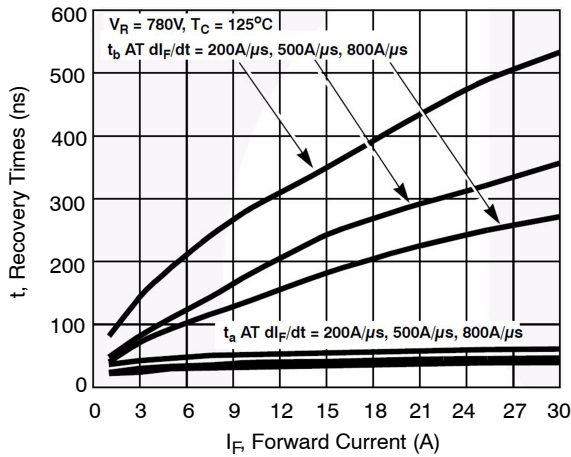


Figure 3. t_a and t_b Curves vs. Forward Current

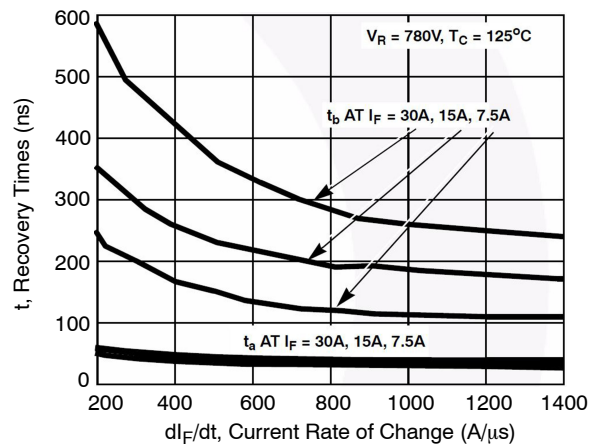


Figure 4. t_a and t_b Curves vs. dl_F/dt

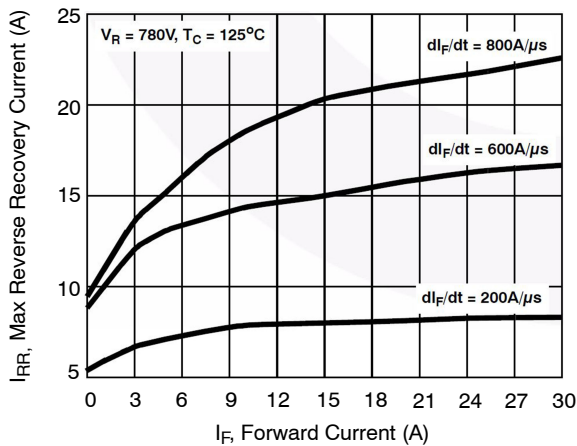


Figure 5. Maximum Reverse Recovery Current vs. Forward Current

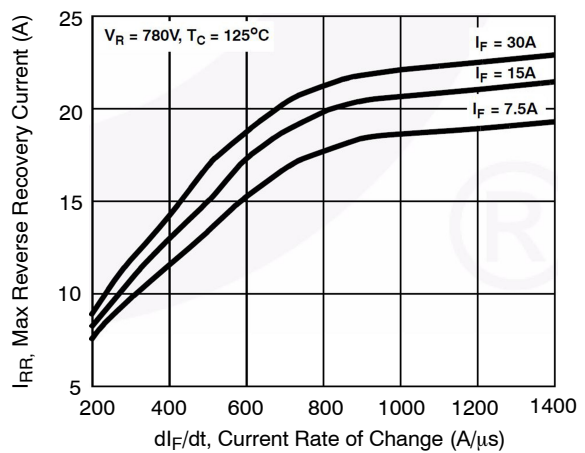


Figure 6. Maximum Reverse Recovery Current vs. dl_F/dt

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TYPICAL PERFORMANCE CURVES (continued)

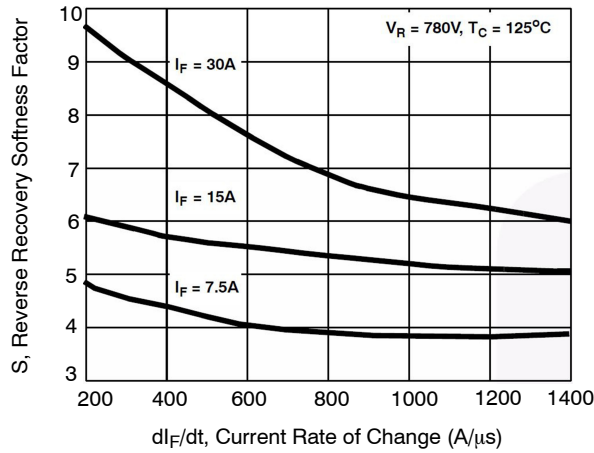


Figure 7. Reverse Recovery Softness Factor vs. dI_F/dt

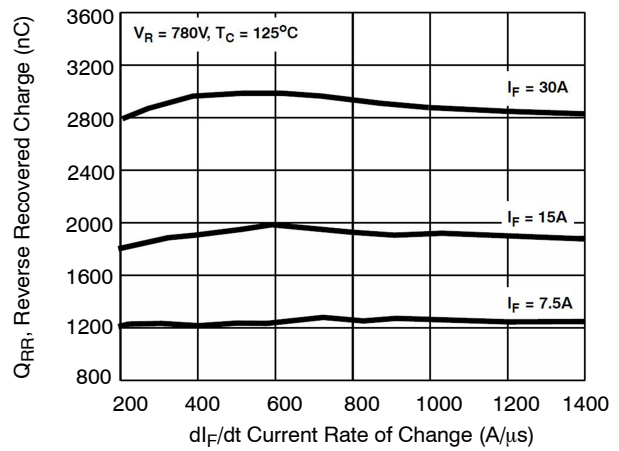


Figure 8. Reverse Recovered Charge vs. dI_F/dt

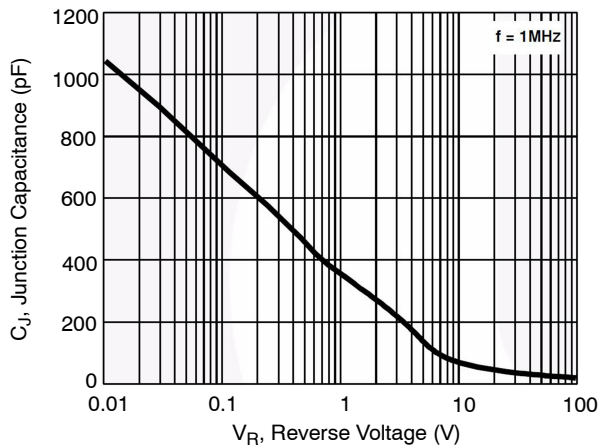


Figure 9. Junction Capacitance vs. Reverse Voltage

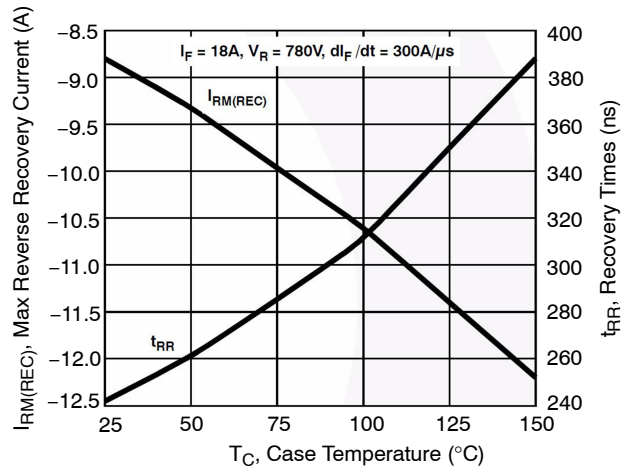


Figure 10. Reverse Recovery Current and Times vs. Case Temperature

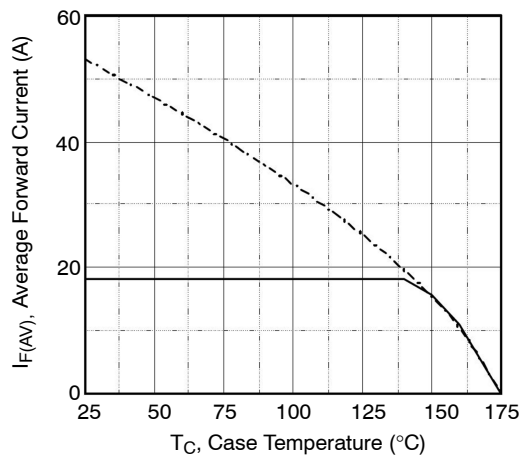


Figure 11. DC Current Derating Curve

TYPICAL PERFORMANCE CURVES (continued)

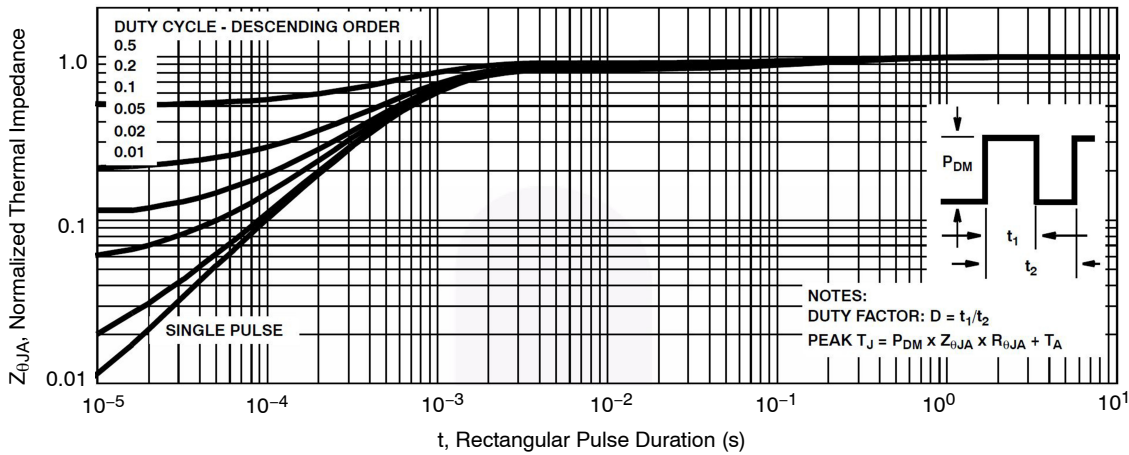


Figure 12. Normalized Maximum Transient Thermal Impedance

TEST CIRCUIT AND WAVEFORMS

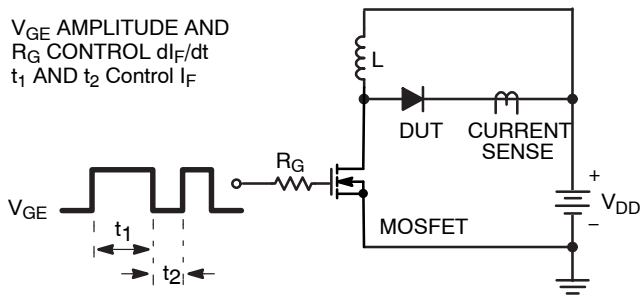


Figure 13. t_{rr} Test Circuit

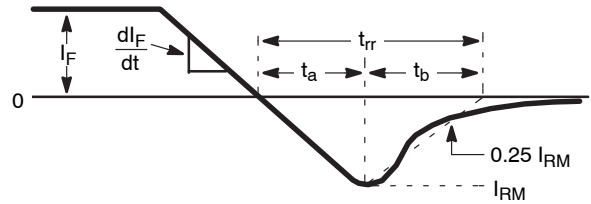


Figure 14. t_{rr} Waveforms and Definitions

- $I = 1 \text{ A}$
- $L = 40 \text{ mH}$
- $R < 0.1 \ \Omega$
- $V_{DD} = 50 \text{ V}$
- $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
- $Q_1 = \text{IGBT (} BV_{CES} > \text{DUT } V_{R(AVL)})$

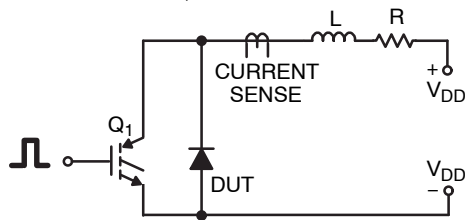


Figure 15. Avalanche Energy Test Circuit

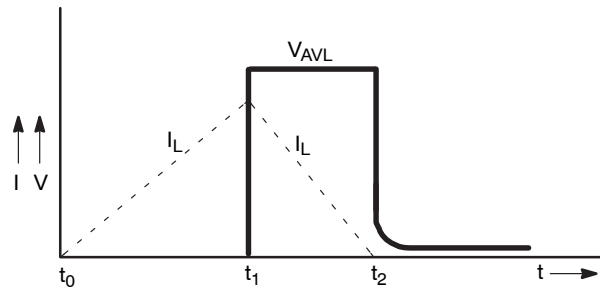
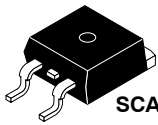


Figure 16. Avalanche Current and Voltage Waveforms

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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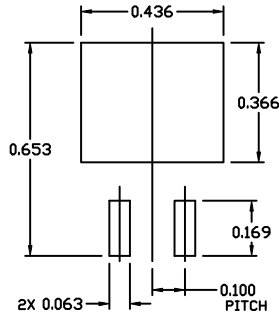
SCALE 1:1

D²PAK-3 (TO-263, 3-LEAD)

CASE 418AJ

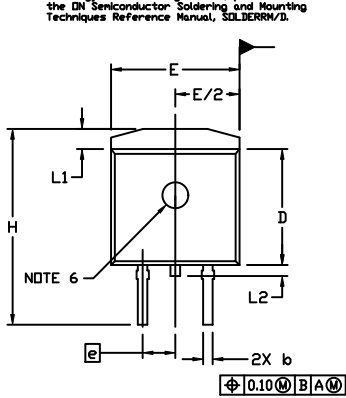
ISSUE E

DATE 25 OCT 2019



RECOMMENDED MOUNTING FOOTPRINT

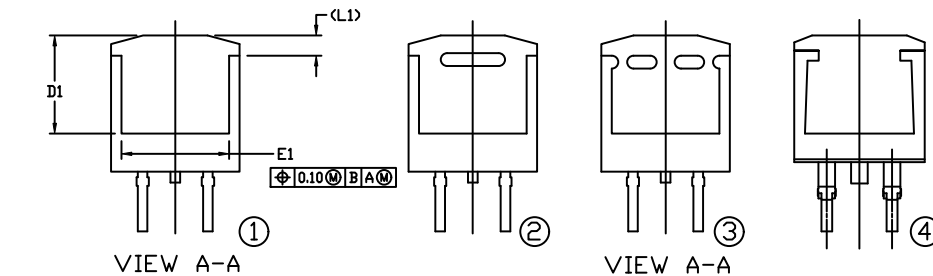
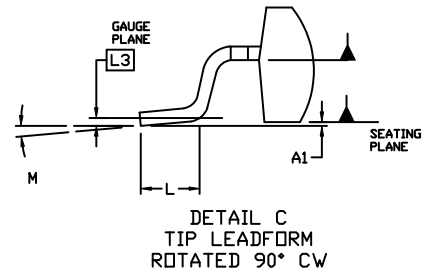
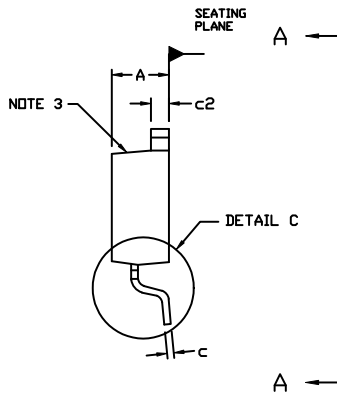
For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SD_1066M/D.



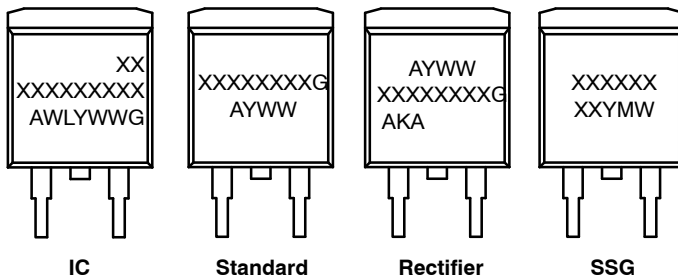
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. CHAMFER OPTIONAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1, AND E1.
6. OPTIONAL MOLD FEATURE.
7. Ⓛ, Ⓜ ... OPTIONAL CONSTRUCTION FEATURE CALL OUTS.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.160	0.190	4.06	4.83
A1	0.000	0.010	0.00	0.25
b	0.020	0.039	0.51	0.99
c	0.012	0.029	0.30	0.74
c2	0.045	0.065	1.14	1.65
D	0.330	0.380	8.38	9.65
D1	0.260	---	6.60	---
E	0.380	0.420	9.65	10.67
E1	0.245	---	6.22	---
e	0.100	BSC	2.54	BSC
H	0.575	0.625	14.60	15.88
L	0.070	0.110	1.78	2.79
L1	---	0.066	---	1.68
L2	---	0.070	---	1.78
L3	0.010	BSC	0.25	BSC
M	-8°	8°	-8°	8°



GENERIC MARKING DIAGRAMS*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- W = Week Code (SSG)
- M = Month Code (SSG)
- G = Pb-Free Package
- AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	D²PAK-3 (TO-263, 3-LEAD)	PAGE 1 OF 1

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